

MBR2080CTG, MBR2090CTG, MBR20100CTG

Switch-mode Power Rectifiers

This series uses the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

Features

- 20 A Total (10 A Per Diode Leg)
- Guard-Ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- Shipped 50 units per plastic tube
- These Devices are Pb-Free and are RoHS Compliant*

Mechanical Characteristics:

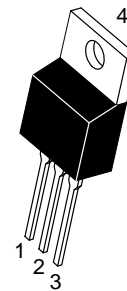
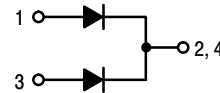
- Case: Epoxy, Molded
- Weight: 1.9 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



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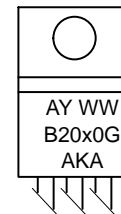
www.onsemi.com

SCHOTTKY BARRIER RECTIFIERS 20 AMPERES 80–100 VOLTS



TO-220
CASE 221A
STYLE 6

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- B20x0 = Device Code
- x = 8, 9 or 10
- G = Pb-Free Device
- AKA = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	MBR			Unit
		2080CT	2090CT	20100CT	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	80	90	100	V
Average Rectified Forward Current (Rated V_R) $T_C = 133^\circ\text{C}$	$I_{F(AV)}$	10			A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz) $T_C = 133^\circ\text{C}$	I_{FRM}	20			A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150			A
Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz)	I_{RRM}	0.5			A
Operating Junction Temperature (Note 1)	T_J	-65 to +175			$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +175			$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000			V/ μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Case	$R_{\theta JC}$	2.0	$^\circ\text{C}/\text{W}$
Junction-to-Ambient	$R_{\theta JA}$	60	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 10$ Amps, $T_C = 125^\circ\text{C}$) ($i_F = 10$ Amps, $T_C = 25^\circ\text{C}$) ($i_F = 20$ Amps, $T_C = 125^\circ\text{C}$) ($i_F = 20$ Amps, $T_C = 25^\circ\text{C}$)	V_F	0.75 0.85 0.85 0.95	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^\circ\text{C}$) (Rated dc Voltage, $T_C = 25^\circ\text{C}$)	i_R	6.0 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

Device	Package	Shipping
MBR2080CTG	TO-220 (Pb-Free)	50 Units / Rail
MBR2090CTG	TO-220 (Pb-Free)	50 Units / Rail
MBR20100CTG	TO-220 (Pb-Free)	50 Units / Rail

MBR2080CTG, MBR2090CTG, MBR20100CTG

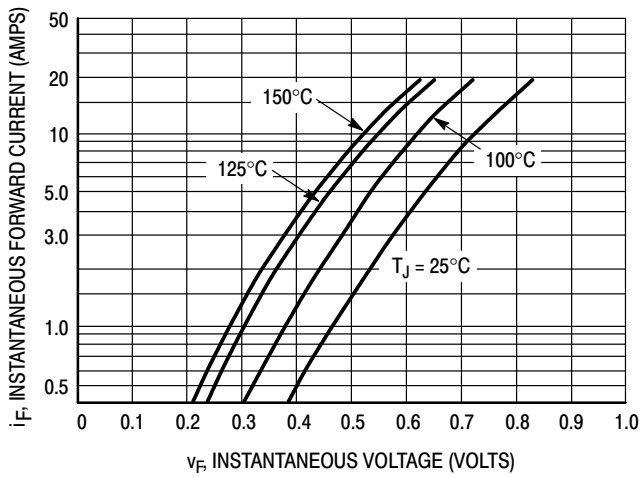


Figure 1. Typical Forward Voltage Per Diode

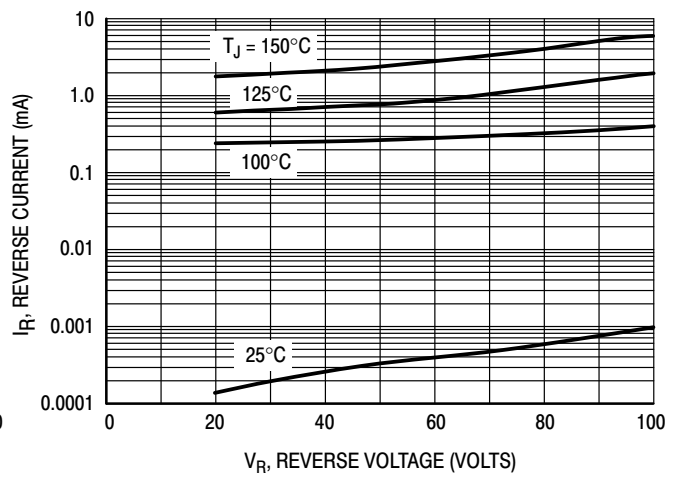


Figure 2. Typical Reverse Current Per Diode

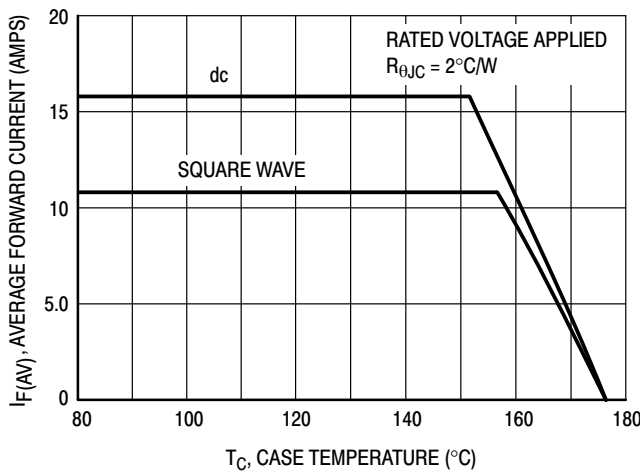


Figure 3. Typical Current Derating, Case, Per Leg

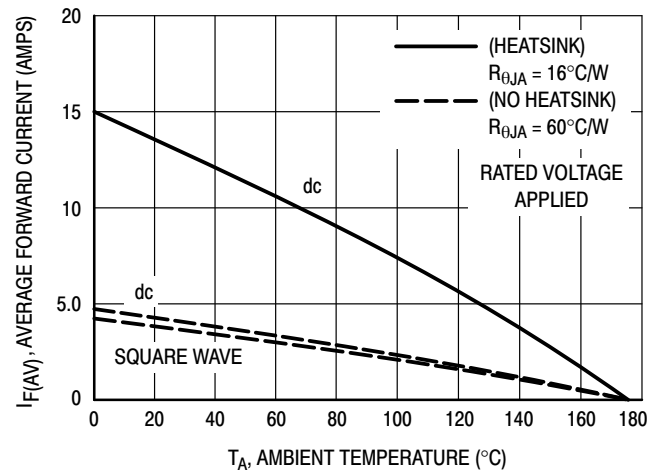


Figure 4. Typical Current Derating, Ambient, Per Leg

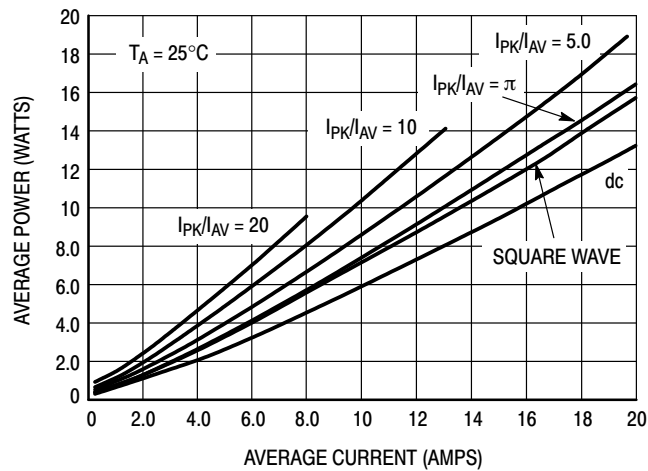
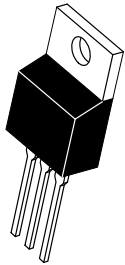


Figure 5. Average Power Dissipation and Average Current

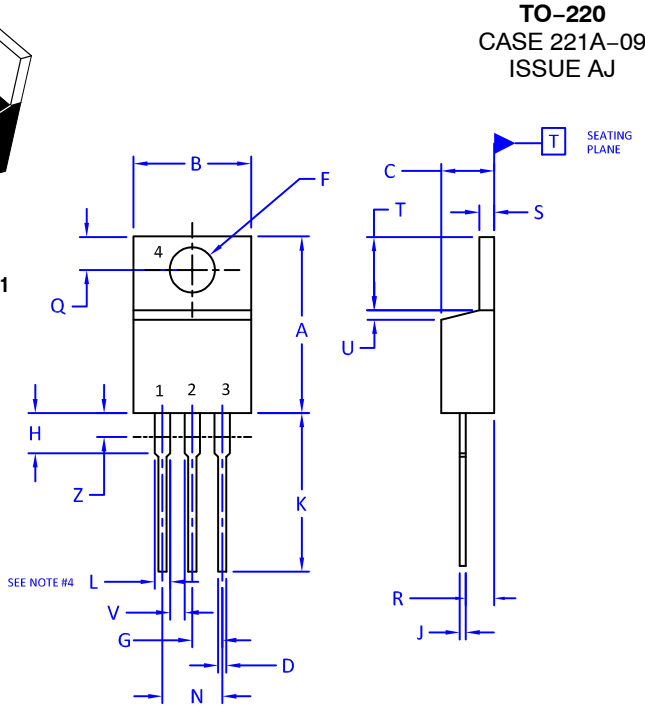
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1



TO-220
CASE 221A-09
ISSUE AJ

DATE 05 NOV 2019

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 2:

- PIN 1. BASE
- 2. EMITTER
- 3. COLLECTOR
- 4. EMITTER

STYLE 3:

- PIN 1. CATHODE
- 2. ANODE
- 3. GATE
- 4. ANODE

STYLE 4:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. MAIN TERMINAL 2

STYLE 5:

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

STYLE 6:

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

STYLE 7:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

STYLE 8:

- PIN 1. CATHODE
- 2. ANODE
- 3. EXTERNAL TRIP/DELAY
- 4. ANODE

STYLE 9:

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 10:

- PIN 1. GATE
- 2. SOURCE
- 3. DRAIN
- 4. SOURCE

STYLE 11:

- PIN 1. DRAIN
- 2. SOURCE
- 3. GATE
- 4. SOURCE

STYLE 12:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. NOT CONNECTED

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